

Atomic layer deposition (ALD)

We carry out ALD processes on wafer, batch and chip level with four different ALD tools.

ALD mini

- R&D of new materials
- Can be loaded manually with 200 mm wafers as well as any wafer and device size below Ø 200 mm

ALD cluster

- Allows automatic handling and successive processing of 25 wafers of 200 mm
- Two chambers are designed respectively for thermal ALD and plasma-enhanced ALD

ALD batch

- 25 wafers of 200 mm can be processed simultaneously with homogeneous quality, aiming for a high throughput

F.A.S.T.-ALD

- Four-chamber system specialized for TSV and µVia production necessary for wafer stacking
- The automatic handling of 200 mm wafers is configured to process a whole 25 wafer batch successively



ALD support for every step from precursor- and process development to pilot production.

Contact

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Fraunhofer Institute for Micro-
electronic Circuits and Systems IMS

Technology Services

Fabrication of demonstrators and prototypes up to pre-production and pilot production.

- Automated, cassette-to-cassette equipment set up for 200 mm wafers (8")
- Area ISO4 cleanroom: >1000 m²
- ISO 9001 certified management system since 1995
- Digital production using modern Manufacturing Execution System (MES)
- Comprehensive system for process monitoring
- Integration of wafers from external foundries
- Capacity: 4500 wafers per year
- Member of the Research Fab Microelectronics Germany (FMD)

Fraunhofer IMS

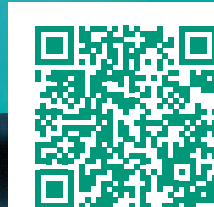
Working on a safe, secure and sustainable future with the help of Smart Sensor Systems:

Our institute consists of numerous research labs, in which we provide ASIC and chip design, CMOS, MEMS, LiDAR development services and many more microelectronic solutions. A seamless path from initial idea to development and production, while maintaining the highest quality and reliability standards, is our offer.

We look forward to giving a long-term support to our customers and be a reliable research and development partner. Fraunhofer IMS provides numerous technologies in four business units: Health, Industry, Mobility, as well as Space and Security.

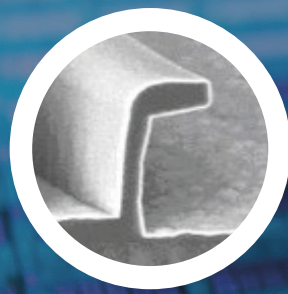
Covering the full process chain

Technology Services

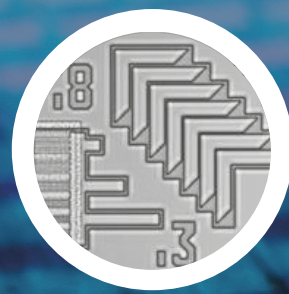




Low temperature
deposition



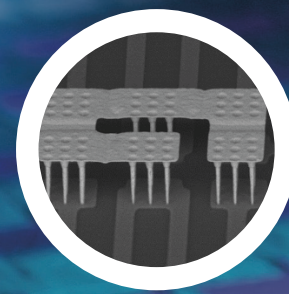
Atomic layer
deposition (ALD)



0.35 μm
lithography



Deep reactive
ion etching (DRIE)



Sacrificial etching



3D integration

From idea to platform

Our services to support your photonic integrated circuit idea at all stages: from first draft to pilot fabrication.

Our services include:

- Device, system design and simulation
- Process development
- Chip fabrication to pilot fabrication
- Device characterization
- Process transfer

Our technology platform is accessible via R&D collaborations and contracting. We are also open to collaborative projects with public funding.

Photonics and electronics made on one manufacturing platform.

Post-CMOS photonic platform

The Fraunhofer IMS post-CMOS compatible SiN-photonics platform offers low-loss components with a broad choice of device geometries and customized options.

Our photonics platform includes integration options of new materials. We use back-end-of-line processes to enable direct interaction of photonics on CMOS wafers.

The dielectric waveguide materials support a broad range of wavelengths from 370 nm - 3 μm . Layers thicknesses and material types can be customized.

Process chain technologies

Process step	Application examples	Specification
Deposition	<ul style="list-style-type: none">■ Functional / sensitive layers■ Isolating / conductive layers■ Layer stack for biomedical encapsulation via ALD■ Temperature sensitive applications	<ul style="list-style-type: none">■ CVD: SiO₂, SiN, Si (B, P, Ge), Ge, aSi, B, W■ PVD: Ti/TiN, TiW, Cu, AlSi, AlCu■ ICP: aSi, SiO₂, SiN, DLC■ ALD: Al₂O₃, Ta₂O₅, ZnO, AZO, TiAlCN, TiN, Ru, MoS₂, WS₂, SiO₂, Cu■ Thermal: SiO₂
Lithography	<ul style="list-style-type: none">■ Converting all necessary layers into an adequate layout■ Transferring alignment marks and test structures	<ul style="list-style-type: none">■ 0.35 μm resolution■ 8" Wafer Stepper■ 8" Mask Aligner■ Backside-alignment possible■ Stitching
Etching	<ul style="list-style-type: none">■ Sacrificial layer technology■ Etching of deep holes / trenches	<ul style="list-style-type: none">■ Wet chemical■ DRIE■ Ion Beam Milling / Etching■ Isotropic release etch (XeF₂, HF)■ Plasma enhanced etching

Process step	Application examples	Specification
3D integration	<ul style="list-style-type: none">■ CMOS single photon avalanche diodes (CSPAD) detector for light imaging, detection, and ranging (LiDAR)■ Electrical wafer-to-wafer connection through microvias	<ul style="list-style-type: none">■ Wafer thinning■ Wafer-to-wafer-bonding■ Chip-to-chip-bonding■ Chip-to-wafer bonding■ Through Silicon Vias (TSVs)■ 8" Wafer
Metrology and test	<ul style="list-style-type: none">■ Scanning acoustic microscopy to detect voids at the interface between two bonded wafers■ Electric characterisation■ Electro-optical characterisation	<ul style="list-style-type: none">■ Void inspection■ Electrical wafer testing■ Surface profiling■ Sheet resistance■ Layer thickness, CD, and overlay measurements■ Chip to wafer■ Through Silicon Vias (TSVs)